

output side respectively of the semiconductor element respectively formed, a first ground metal plate, and one or more second dielectric substrates located between said first dielectric substrate and the first ground metal, wherein:

a second ground metal is provided on the surface of each of the second dielectric substrates, and the second ground metal provided on the surface of at least one of the second dielectric substrates being adjacent to the first dielectric substrate is formed in the shape in which a part of the second ground metal opposite to the transmission line of said matching circuit on the output side is removed while maintaining the dielectric substrate adjacent to the part of the second ground metal that is removed.

4. (Amended) A high frequency circuit module according to Claim 3, wherein:

said second ground metal is formed in the shape in which a part opposite to said transmission line of said matching circuit on the input side is removed while maintaining the dielectric substrate adjacent to the part removed.

7. (Amended) A high frequency circuit module provided with a first dielectric substrate on which a semiconductor element and matching circuits on the input side and on the output side respectively of the semiconductor element respectively formed, a first ground metal plate, and one or more second dielectric substrates located between said first dielectric substrate and the first ground metal, wherein: a second ground metal is provided on the surface of each of the second dielectric substrates, and the second ground metal provided on the surface of at least one of the second dielectric substrates being adjacent to the first dielectric substrate is formed in the shape in which a part of the second ground metal opposite to the transmission line of said matching circuit on the input side is removed while maintaining the dielectric substrate adjacent to the part of the second ground metal that is removed.

8. (Amended) A high frequency circuit module according to Claim 7, wherein:

the second ground metal is formed in the shape in which a part opposite to said transmission line of said matching circuit on the output side is removed while

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cont. maintaining the dielectric substrate adjacent to the part removed.

--17. A high frequency circuit module having a first dielectric substrate on which a semiconductor element, an input-side matching circuit and output-side matching circuit are formed;

a first ground metal plate;

a second dielectric substrate located between said first dielectric substrate and said first ground metal; and

Q5 a second ground metal provided on the surface of said second dielectric substrate such that said second ground metal is located between said first dielectric substrate and said second dielectric substrate and is adjacent to said first dielectric substrate, wherein a portion of said second ground metal is removed from the surface of said second dielectric substrate, said portion facing said output-side matching circuit provided on said first dielectric substrate such that said output side matching circuit faces said second dielectric substrate.

--18. A high frequency circuit module as claimed in claim 17, wherein said second ground metal is formed such that said

portion of said second ground metal is removed while maintaining the second dielectric substrate below said portion of said second ground metal that is removed.

--19. A high frequency circuit module as claimed in claim 17, further comprising at least one additional dielectric substrate located between said second dielectric substrate and said first ground metal.

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cont.* --20. A high frequency circuit module as claimed in claim 18, further comprising at least one additional dielectric substrate located between said second dielectric substrate and said first ground metal.

--21. A high frequency circuit module as claimed in claim 17, wherein said portion of said second ground metal that is removed faces a transmission line portion of said output-side matching circuit.

--22. A high frequency circuit module as claimed in claim 17, wherein another portion of said second ground metal is removed from the surface of said second dielectric

substrate, said portion facing said input-side matching circuit.

--23. A high frequency circuit module as claimed in claim 22, wherein said second ground metal is formed such that said another portion of said second ground metal is removed while maintaining the second dielectric substrate below said another portion of said second ground metal that is removed.

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cont.*
--24. A high frequency circuit module as claimed in claim 22, further comprising at least one additional dielectric substrate located between said second dielectric substrate and said first ground metal.

--25. A high frequency circuit module as claimed in claim 23, further comprising at least one additional dielectric substrate located between said second dielectric substrate and said first ground metal.

--26. A high frequency circuit module as claimed in claim 22, wherein said another portion of said second ground metal that is removed faces a transmission line portion of said input-side matching circuit.--
